EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S6	807	TSUBOI-TAKASHI.in. YAMAGATA-KENJI.in. SAKAGUCHI-KIYOFUMI.in. YANAGITA-KAZUTAKA.in. SUGAI-TAKAShi.in. TAKANASHI-KAZUHITO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 13:39
S7	1411	electrode and (substrate wafer chip workpiece) and (((flow near2 (distribut$3)) (shower near2 head) (dispersion near2 (device)) (perforat$3 near2 flow) (plurality near2 hole) (punctur$3) (baffle) (diffus$3 near2 flow)) with (electrolyte solution mixture solvent))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 13:47
S8	1650	electrode and (substrate wafer chip workpiece) and (((flow near2 (distribut$3)) (shower near2 head) (dispersion near2 (device)) (perforat$3 near2 flow) (plurality near2 (hole opening)) (punctur$3) (baffle) (diffus$3 near2 flow)) with (electrolyte solution mixture solvent))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:14
S9	1	S8 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 13:47
S12	1206	S8 and (@ad<"20021226" @pd<"20021226")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 13:51
S13	28	S8 and (@ad<"20021226" @pd<"20021226") and (bubble near2 (avoid remove ("remove from" adj (surface substrate wafer)) (good near contact)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:07
S14	11	S8 and (@ad<"20021226" @pd<"20021226") and (bubble near2 (avoid remove ("remove from" adj (surface substrate wafer)) (good near contact))) and 205/80-333.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:07

S15	1843	(electrode anode cathode) and (substrate wafer chip workpiece) and (((flow near2 (distribut$3)) (shower near2 head) (dispersion near2 (device)) (perforat$3 near2 flow) (plurality near2 (hole opening)) (punctur$3) (baffle) (diffus$3 near2 flow)) with (electrolyte solution mixture solvent))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 11:13
S16	30	S15 and (@ad<"20021226" @pd<"20021226") and (bubble near2 (avoid remove ("remove from" adj (surface substrate wafer)) (good near contact)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:07
S17	13	S15 and (@ad<"20021226" @pd<"20021226") and (bubble near2 (avoid remove ("remove from" adj (surface substrate wafer)) (good near contact))) and 205/80-333.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:22
S18	14196	electrode and (substrate wafer chip workpiece) and (((flow near2 (distribut$3)) (shower near2 head) (inject$3) (dispersion near2 (device)) (perforat$3 near2 flow) (plurality near2 (hole opening)) (punctur$3) (baffle) (diffus$3 near2 flow)) with (electrolyte solution mixture solvent))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:16
S24	81	(electrode anode cathode) and (substrate wafer chip workpiece) and (((flow near2 (distribut$3)) (shower near2 head)(dispersion near2 (device)) (perforat$3 near2 flow) (plurality near2 (hole opening)) (punctur$3) (baffle) (diffus$3 near2 flow)) with (electrolyte solution mixture solvent) with (inject$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:20
S25	0	S24 and (@ad<"20021226" @pd<"20021226") and (bubble near2 (avoid remove ("remove from" adj (surface substrate wafer)) (good near contact))) and 205/80-333.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:20

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S26	171	(electrode anode cathode) and (substrate wafer chip workpiece) and ((shower near2 head) with (electrolyte solution mixture solvent))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:22
S27	4	S26 and (@ad<"20021226" @pd<"20021226") and 205/80-333.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:47
S28	686	((horizontal) near2 (wafer semiconductor workpiece substrate)) and ((two "more than one" "at least two" "one or more" multiple several three plurality) near2 ((shower adj head) (jet near nozzle) nozzle))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:51
S29	21	((horizontal) near2 (wafer semiconductor workpiece substrate)) and ((two "more than one" "at least two" "one or more" multiple several three plurality) near2 ((shower adj head) (jet near nozzle) nozzle)) and (@ad<"20021226" @pd<"20021226") and 205/80-333.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 16:55
S31	3360	205/133,147,316-333.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 16:57
S32	3230	205/133,147,316-333.ccls. and (@ad<"20021226" @pd<"20021226")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 16:58
S33	41	S32 and ((two "more than one" "at least two" "one or more" multiple several three plurality) near2 ((shower adj head) (jet near nozzle) nozzle))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:24

S34	0	S32 and ((imping$4 near2 flow) near2 (both near (side surface)) with (substrate wafer workpiece semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 17:49
S35	0	S32 and ((imping$4 near2 flow) near2 ((both two (top and bottom)) near2 (side surface)) with (substrate wafer workpiece semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 17:50
S36	807	TSUBOI-TAKASHI.in. YAMAGATA-KENJI.in. SAKAGUCHI-KIYOFUMI.in. YANAGITA-KAZUTAKA.in. SUGAI-TAKASHi.in. TAKANASHI-KAZUHITO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:14
S37	1411	electrode and (substrate wafer chip workpiece) and (((flow near2 (distribut$3)) (shower near2 head) (dispersion near2 (device)) (perforat$3 near2 flow) (plurality near2 hole) (punctur$3) (baffle) (diffus$3 near2 flow)) with (electrolyte solution mixture solvent))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:24
S38	1	S37 and S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:16
S39	1	S37 and S36 and canon.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:16
S40	31	S32 and canon.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:17
S41	11	S32 and canon.as. and (shower)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:21

S42	12	S31 and canon.as. and (shower)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:21
S43	80364	((two "more than one" "at least two" "one or more" multiple several three plurality) near2 ((shower adj head) (jet near nozzle) nozzle)) and (@ad<"20021226" @pd<"20021226")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:25
S44	7770	S43 and (electrode anode cathode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:25
S45	44	S44 and (anode near2 (spray shower nozzle)) and (cathode near2 (spray shower nozzle))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 18:27
S46	71	(electrode anode cathode) and (substrate wafer chip workpiece) and (((flow near2 (distribut$3)) (shower near2 head) (dispersion near2 (device)) (perforat$3 near2 flow) (plurality near2 (hole opening)) (punctur$3) (baffle) (diffus$3 near2 flow)) with (electrolyte solution mixture solvent)) and (porous near layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 11:18
S47	1	(electrode anode cathode) and (substrate wafer chip workpiece) and (((flow near2 (distribut$3)) (shower near2 head) (dispersion near2 (device)) (perforat$3 near2 flow) (plurality near2 (hole opening)) (punctur$3) (baffle) (diffus$3 near2 flow)) with (electrolyte solution mixture solvent)) and (porous near layer) and (SOI (silicon adj insulator) (semiconductor adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 11:19

S48	28	(electrode anode cathode) and (substrate wafer chip workpiece) and (((flow near2 (distribut$3)) (shower near2 head) (dispersion near2 (device)) (perforat$3 near2 flow) (plurality near2 (hole opening)) (punctur$3) (baffle) (diffus$3 near2 flow)) with (electrolyte solution mixture solvent)) and (SOI (silicon adj insulator) (semiconductor adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 11:29
S49	13	(electrode anode cathode) and (substrate wafer chip workpiece) and (porous near layer) and (non-porous near layer) and (stack) and (bond join) and ((electrolyte solution mixture solvent)) and (SOI (silicon adj insulator) (semiconductor adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 11:43
S50	807	TSUBOI-TAKASHI.in. YAMAGATA-KENJI.in. SAKAGUCHI-KIYOFUMI.in. YANAGITA-KAZUTAKA.in. SUGAI-TAKAShi.in. TAKANASHI-KAZUHITO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 11:40
S51	10	(electrode anode cathode) and (substrate wafer chip workpiece) and (porous near layer) and (non-porous near layer) and (stack) and (bond join) and ((electrolyte solution mixture solvent)) and (SOI (silicon adj insulator) (semiconductor adj insulator)) and S50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 11:42
S52	39	(electrode anode cathode) and (substrate wafer chip workpiece) and (porous near layer) and (non-porous near layer) and (stack) and (bond$3 join$3 bond join) and ((electrolyte solution mixture solvent)) and (SOI (silicon adj insulator) (semiconductor adj insulator)) and S50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 13:46

S53	45	(electrode anode cathode) and (substrate wafer chip workpiece) and (porous near layer) and (non-porous near layer) and (stack) and (bond$3 join$3) and ((electrolyte solution mixture solvent)) and (SOI (silicon adj insulator) (semiconductor adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 11:43
S54	807	TSUBOI-TAKASHI.in. YAMAGATA-KENJI.in. SAKAGUCHI-KIYOFUMI.in. YANAGITA-KAZUTAKA.in. SUGAI-TAKAShi.in. TAKANASHI-KAZUHITO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 13:46
S55	39	(electrode anode cathode) and (substrate wafer chip workpiece) and (porous near layer) and (non-porous near layer) and (stack) and (bond$3 join$3 bond join) and ((electrolyte solution mixture solvent)) and (SOI (silicon adj insulator) (semiconductor adj insulator)) and S54 and (jet inject$3 shower)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 14:07
S56	4	(electrode anode cathode) and (substrate wafer chip workpiece) and (porous near layer) and (non-porous near layer) and (stack) and (bond$3 join$3 bond join) and ((electrolyte solution mixture solvent)) and (SOI (silicon adj insulator) (semiconductor adj insulator)) and S54 and ((jet inject$3 shower) same (anode electrode cathode electrolyte))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 14:25
S57	14	("5371037"|"5458755"|"5951833" |"6246068"|"6258240"|"6417069" |"6547938").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 14:25
S58	7	(US-6547938-$ or US-6417069-$ or US-6258240-$ or US-6246068-$ or US-5951833-$ or US-5458755-$ or US-5371037-$).did.	USPAT	OR	ON	2006/07/20 14:25
S59	5	S58 not S55	USPAT	OR	ON	2006/07/20 14:35
S60	1	S58 not S55 and ((jet inject$3 shower) same (anode electrode cathode electrolyte))	USPAT	OR	ON	2006/07/20 14:35